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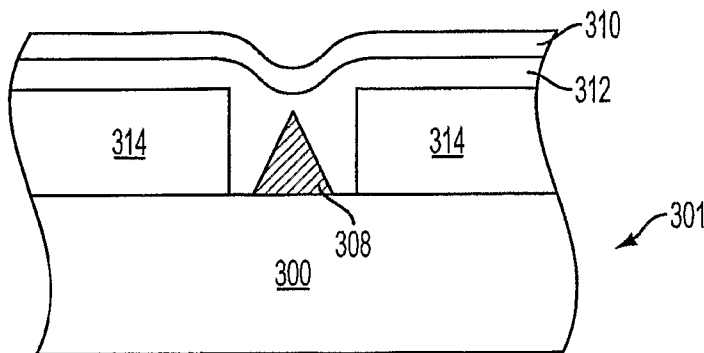
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(54) Title: REPRODUCIBLE RESISTANCE VARIABLE INSULATING MEMORY DEVICES AND METHODS FOR FORMING SAME



(57) Abstract: The present invention relates to the use of a shaped bottom electrode in a resistance variable memory device (301). The preferably cone-like shaped bottom electrode (308) ensures that the thickness of the insulating material (312) at the tip of the bottom electrode is thinnest, creating the largest electric field at the tip of the bottom electrode. The arrangement of electrodes (308, 310) and the structure of the memory element makes it possible to create conduction paths with stable, consistent and reproducible switching and memory properties in the memory device.

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